## Amendment of the Claims

Please cancel claims 37-40.

- 1. (Original) A method of making a microelectromechanical system device comprising: releasing a micromover component; and coating the micromover component with a first self-aligned film after releasing the micromover component.
- 2. (Original) The method of claim 1, wherein the step of coating comprises selectively depositing a coating composition only on the micromover component.
- 3. (Original) The method of claim 1, wherein the film comprises at least one of a polymer, PMMA and an epoxy photoresist.
- 4. (Original) The method of claim 3, wherein the polymer is thermoplastic.
- 5. (Original) The method of claim 3, wherein the polymer is thermoset.
- 6. (Original) The method of claim 1, wherein coating the micromover component comprises adjusting a coating parameter to control the film thickness.
- 7. (Original) The method of claim 6, wherein adjusting a coating parameter comprises selecting a solid to solvent ratio.
- 8. (Original) The method of claim 6, wherein adjusting a coating parameter comprises selecting an amount of film material to deposit.
- 9. (Original) The method of claim 1, further comprising plasma treating a surface of the micromover component prior to coating.
- 10. (Original) The method of claim 9, further comprising applying an adhesion promoter

to the micromover component after plasma treating.

- 11. (Original) The method of claim 1, further comprising coating the micromover component with a second self-aligned film.
- 12. (Original) The method of claim 11, wherein the second self-aligned film comprises a different material from the first self-aligned film.
- 13. (Original) The method of claim 12, wherein one of the self-aligned films comprises a thermoplastic polymer and the other comprises a thermoset polymer.
- 14. (Original) The method of claim 12, wherein the first self-aligned film and the second self-aligned film have different hardness.
- 15. (Original) The method of claim 12, wherein the first self-aligned film and the second self-aligned film have different glass transition temperatures.
- 16. (Original) The method of claim 1, further comprising bonding a wafer having at least one contact probe or AFM tip opposite the self-aligned film.
- 17. (Original) The method of claim 16, further comprising fabricating a contact atomic resolution storage device.
- 18. (Original) The method of claim 1, wherein the first self-aligned film is adapted for data storage, anti-wear, anti-reflective, desiccant or an anti-stiction.
- 19. (Previously Withdrawn) A mass storage device comprising: at least one micromover including a self-aligned film adapted to store data; and at least one contact probe or AFM tip located opposite the at least one micromover and adapted to write in the self-aligned film.

- 20. (Previously Withdrawn) The mass storage device of claim 19, wherein the selfaligned film comprises a polymer.
- 21. (Previously Withdrawn) The mass storage device of claim 20, wherein the polymer comprises at least one of thermoplastic, PMMA and an epoxy photoresist.
- 22. (Previously Withdrawn) The mass storage device of claim 20, wherein the polymer is thermoset.
- 23. (Previously Withdrawn) The mass storage device of claim 19, further comprising a plurality of self-aligned films.
- 24. (Previously Withdrawn) The mass storage device of claim 23, wherein the plurality of self-aligned films comprises at least two different film materials.
- 25. (Previously Withdrawn) The mass storage device of claim 24, wherein one of the self-aligned films comprises a thermoplastic polymer and the other comprises a thermoset polymer.
- 26. (Previously Withdrawn) The mass storage device of claim 24, wherein the at least two different film materials have different hardness.
- 27. (Previously Withdrawn) The mass storage device of claim 24, wherein the at least two different film materials have different glass transition temperatures.
- 28. (Previously Withdrawn) A mass storage device comprising: at least one means for storing data having at least one self-aligned film; and means for writing data in the at least one self-aligned film.
- 29. (Previously Withdrawn) The mass storage device of claim 28, further comprising a means for moving the means for storing data.

- 30. (Previously Withdrawn) The mass storage device of claim 29, further comprising a means for reducing wear of the means for writing data.
- 31. (Previously Withdrawn) An integrated circuit comprising: at least one micromover having a self-aligned film adapted to store data; at least one contact probe or AFM tip located opposite the at least one micromover, the at least one contact probe or AFM tip adapted to write in the self-aligned film; and at least one circuit to control the movement of the at least one micromover.
- 32. (Previously Withdrawn) The integrated circuit of claim 31, wherein the integrated circuit comprises a contact atomic resolution storage device.
- 33. (Previously Withdrawn) A method of storing data comprising: moving a micromover having a self-aligned data storage film; and heating at least one contact probe or AFM tip to a first temperature to make an indentation in the self-aligned data storage film.
- 34. (Previously Withdrawn) The method of claim 33, further comprising repeating the steps of moving and heating a plurality times.
- 35. (Previously Withdrawn) The method of claim 34, further comprising erasing previously written data by heating the self-aligned data storage film to a second temperature to melt the film and remove the indentations.
- 36. (Previously Withdrawn) The method of claim 35, further comprising reusing the self-aligned data storage film by moving the micromover and heating at least one contact probe or AFM tip to the first temperature to make an indentation in the self-aligned data storage film.
- Cancelled).
- 38. (Cancelled).

- 39. (Cancelled).
- 40. (Cancelled).
- 41. (Previously Withdrawn) A semiconductor device comprising at least one component having a self-aligned polymer film thereon.
- 42. (Previously Withdrawn) The semiconductor device of claim 41, wherein the semiconductor device comprises one of a display, a bio-chip, a surface microelectromechanical system device and a bulk microelectromechanical system device.